Adhesion Considerations in Designing Dielectric Materials for Advanced Packaging Applications

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### Outline

- Background: Materials' Requirements for Advanced Packaging Applications
- □ Impact of Polymer Functional Group on Adhesion
- **Role of Adhesion Promoter**
- Reliability Studies
- **Resolution**
- Summary

**Dielectric Material Requirements for Advanced Packaging** 

Low Thermal Shrinkage

Low Temperature Cure

Low residual stress and warpage control

Good Thermal, Mechanical, and Overall Film Properties

**Rheological Properties – to improve planarization** 

Multiple Patterning Options – improved resolution to ensure scalability

Good adhesion to multiple substrates is key for enhanced reliability

Adhesion Considerations in Typical Organic Dielectric Materials





Highly polar functional groups of PBO precursor and Polyamic acid/ester (PI precursor) useful for anchoring to enhance adhesion with substrate

Adhesive properties of fully cyclized polyimide?



Polyamic acid/ester (PI) Precursor



Fully Cyclized Polyimide

### **FUJIFILM** Impact of Polymer Functionality on Adhesion



### **Improving Polymer Adhesion: Role of Adhesion Promoter**

Polymer adhesion to substrates can be quite complex but typically occurs by chemical and/or physical interaction of adhesion promoter with both polymer and substrate.



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### **Mechanism of Adhesion**

• Adhesion promoter connects polymer to substrate through chemical bonds with reactive groups on alternate ends of adhesion promoter.



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### **Adhesion Promoter Examples**



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**Improving Polymer Adhesion via Adhesion Promoter** 



Improved adhesion could be achieved using structurally modified adhesion promoters

Impact of improved adhesion on reliability

### **Board Level Reliability Data: Summary**

• Drop Test

Under Fill	Chip Size
	5X5 mm <sup>2</sup>
No	10/10 Chips
	(100%)
Yes	10/10 Chips
	(100%)



No electrical failure detected. No open daisy chain structure or voiding in solder bumps observed in cross section



• TCT ([-55 °C / +125 °C )

Under Fill	Chip Size
	5X5 mm <sup>2</sup>
Yes	10/10 Chips
	(100%) 500 cycle



### **FUJIFILM** THB Inline Leakage Current Measurement (after 196 hours of Storage)





Voltage: 5V

10 um L/S 5um high Interdigital electrode area 2 x 14.65 mm Temperature: 85°C/ RH:85%

- Material was processable on copper inter-dielectric electrodes
- without any copper attack or corrosion
- Sample showed no corrosion of the copper after the biased storage. No evidence of dendrite
- Leakage current was stable during the storage of 196 hours

### **FUJIFILM** Cross Sectional SEM Analysis after 1000 Hours of HTS (150°C)



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### **Overall Film Properties (Cured at 170°C/2 hrs.)**

CTE (50 ~ 125°C)	60 ppm/°C	
Young Modulus (room temperature)	3.3 GPa	
Poisson ratio	0.4	
Residual Stress, MPa	13	
Elongation-to-break	60%	
Tg (DMA by storage modulus)	247°C	
Thormal stability	2% weight loss: 315°C	
mermai stability	5% weight loss: 390°C	
Thermal Shrinkage (Post 170°C cure)	<5%	
Moisture uptake (80%RH/80°C)	0.97%	
Dielectric constant/Dielectric loss (1-20 GHz)	2.8/0.02	
Leakage current (Before and after 250 hrs.		
THB)	< 1.UE-U0A	
Dool strongth	1.3KgF/cm (Before HAST)	
reel stiength	0.6KgF/cm (after 500 hours HAST)	

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1.9 μm Vias in 5μm Film E=150 mJ/cm<sup>2</sup> (0.18 NA i-Line) (Substrate: PVD-Cu)



5 μm via in 12 μm Film 400 mJ/cm<sup>2</sup> (0.45 NA i-line) (Substrate: PVD-Cu)

**Resolution Capability** 



5 μm via in 8μm Film 200 mJ/cm<sup>2</sup> (LDI exposure) (Substrate: PVD-Cu)



%Loss during cure %Loss during development %Loss development + cure Typical %Loss Range of PI precursor 40 %Film Thickness Loss 35 30 25 20 15 10 5 Al PVD Cu Virgin Si SiN SiO

Total film Loss due to development and cure processes combined is ~ 6-8%.

#### **Typical Process Conditions**

Substrate Preparation: Varys with substrate type Spin coat: 1000 rpm to 4000 rpm (to cover film thickness range of 5 to 20 μm Soft bake: 90°C/180 seconds Develop & Rinse: 2 puddles (40 to 90 seconds each) in cyclopentanone, followed by 2 puddles (20 to 45 seconds each) in PGMEA Post Exposure Bake: None

Cure: 170°C for 2 hours in nitrogen or air

### **Summary**

- Fully cyclized polyimide demonstrated low thermal shrinkage and low residual stress
- High resolution is demonstrated under i-line and LDI conditions
- Significant improvement in adhesion could be achieved by formulating with appropriate adhesion promoter
- Optimized film passed all reliability properties

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